## NSN 5961-01-107-0970

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**Inclosure Material:** Metal **Overall Length:** Between 0.170 inches and 0.210 inches **Terminal Length:** Between 0.500 inches and 0.750 inches **Overall Diameter:** Between 0.209 inches and 0.230 inches **Internal Configuration:** Junction contact Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-18 **Electrode Internally-electrically Connected To Case:** Gate **Mounting Method: Terminal Terminal Circle Diameter:** 0.100 inches **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 1.5 forward voltage, peak and 0.8 gate trigger voltage, dc **Current Rating Per Characteristic:** 200.00 microamperes forward current, total rms absolute **Maximum Operating Tempurature Per Measurement Point:** 150.0 degrees celsius ambient air **Special Features:** Junction pattern arrangement: pnpn **Precious Material And Location:** Terminal surfaces gold **Precious Material:** Gold

## Test Data Document:

81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

### **Terminal Type And Quantity:**

3 uninsulated wire lead

#### **Specification Data:**

81349-mil-s-19500/419 government specification

Shelf Life:

N/a

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Demilitarization:

No

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